

Appln. No. 10/526,818

Attorney Docket No. 10808-222

## I. Amendments to the Abstract

Please add the following paragraph after the listing of the claims:

## ABSTRACT

A method for producing an integrated PIN photodiode. The PIN photodiode contains a doped region of a first conduction type near the substrate and a doped region that is remote from the substrate. The doped region that is remote from the substrate has a different construction type than the region near the substrate. In addition, an intermediate region provided that is a range between the doped region remote from the substrate and the doped region near the substrate. The intermediate region is undoped or provided with weak doping.